Hex Inverter

(Unbuffered)

The MC74LVX04 is an advanced high speed CMOS unbuffered hex inverter. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 4.1 \text{ ns (Typ)}$ at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.5 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Pb-Free Packages are Available*

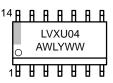


http://onsemi.com

MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A



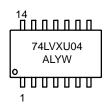


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 M SUFFIX CASE 965



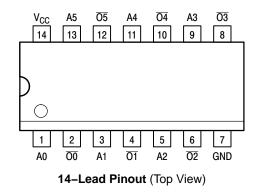
A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



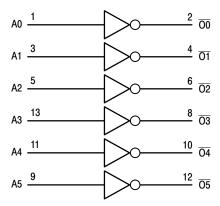


Figure 1. Logic Diagram

PIN NAMES

Pins	Function
An	Data Inputs
On	Outputs

FUNCTION TABLE

An	On
L	H
H	L

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVXU04D	SOIC-14	55 Units / Rail
MC74LVXU04DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74LVXU04DR2	SOIC-14	2500 Tape & Reel
MC74LVXU04DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74LVXU04DT	TSSOP-14*	96 Units / Rail
MC74LVXU04DTR2	TSSOP-14*	2500 Tape & Reel
MC74LVXU04M	SOEIAJ-14	50 Units / Rail
MC74LVXU04MG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74LVXU04MEL	SOEIAJ-14	2000 Tape & Reel
MC74LVXU04MELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb–Free.

MAXIMUM RATINGS

Symbol	Pa	rameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to $V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	V _I < GND	-20	mA
I _{OK}	DC Output Diode Current	V _O < GND	±20	mA
I _{OUT}	DC Output Sink Current		±25	mA
I _{CC}	DC Supply Current per Supply Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10	Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	250	°C/W
P _D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94-V0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 2000	V
I _{Latchup}	Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 4)	±300	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- Tested to EIA/JESD22-A114-A.
 Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	2.0	3.6	V
VI	Input Voltage (Note 5)	0	5.5	V
Vo	Output Voltage (HIGH or LOW State)	0	V _{CC}	V
T _A	Operating Free–Air Temperature	-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$	0	100	ns/V

5. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	$T_A = 25^{\circ}C$			$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	I _{OL} = 50 μA I _{OL} = 50 μA I _{OL} = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Input Leakage Current	V _{in} = 5.5 V or GND	3.6			±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			2.0		20.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$)

				T _A = 25°C		T _A = -40 to 85°C			
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, Input to Output	V _{CC} = 2.7V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.4 7.9	10.1 13.6	1.0 1.0	12.5 16.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15 pF$ $C_L = 50 pF$		4.1 6.6	6.2 9.7	1.0 1.0	7.5 11.0	
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 6)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50 \text{ pF}$ $C_L = 50 \text{ pF}$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

		T _A = 25°C		T _A = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C _{PD}	Power Dissipation Capacitance (Note 7)		18				pF

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/6$ (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

			T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V	
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V	
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V	

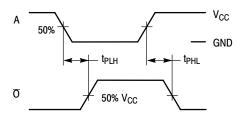
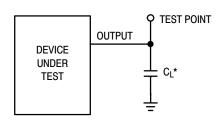


Figure 2. Switching Waveforms

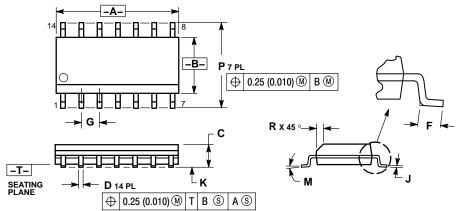


*Includes all probe and jig capacitance

Figure 3. Test Circuit

PACKAGE DIMENSIONS

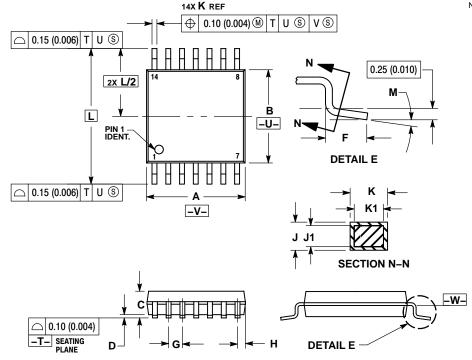
SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE G



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	RS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



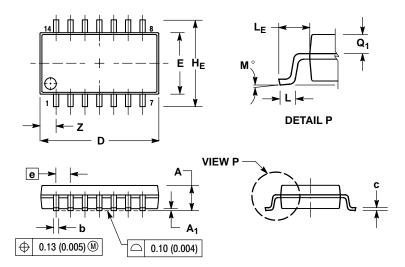
NOTES:

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 MIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	BSC
M	0 °	a °	0 °	80

PACKAGE DIMENSIONS

SOEIAJ-14 **M SUFFIX** CASE 965-01 **ISSUE O**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		MILLIMETERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.18	0.27	0.007	0.011	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27 BSC		0.050	BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10°	
Q ₁	0.70	0.90	0.028	0.035	
Z		1.42		0.056	

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